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- 1 M. DeJarld, J. C. Shin, W. Chern, D. Chanda, K. Balasundaram, J. A. Rogers, X. Li. Formation of High Aspect Ratio GaAs Nanostructures with Metal-Assisted Chemical Etching, *Nano Lett.*, 2011, v. 11, 5259-5263
- 2 US 10147789 B2 2018.12.04
- 3 H. Asoh, S. Kotaka, S. Ono. High-aspect-ratio GaAs pores and pillars with triangular cross section, *Electrochem. Commun.*, 2011, v. 13, 458-461
- 4 MD 4840 B1 2023.01.31
- 5 US 7182812 B2 2007.02.27
- 6 S. Kumar, R. Singh. Nanofunctional gallium oxide (Ga_2O_3) nanowires/nanostructures and their applications in nanodevices, *Phys. Status Solidi RRL*, 2013, v. 7, nr. 10, p. 781-792
- 7 Eduard Monaico. Formation of low-dimensional structures on InP under fast anodic etching, *Conferință Științifică a Colaboratorilor, Doctoranzilor și Studenților UTM*, 27 noiembrie 2015, vol. 1, p. 179-182, <<http://repository.utm.md/handle/5014/697>>